



# STP9NC65 STP9NC65FP

N-CHANNEL 650V - 0.75Ω - 8A TO-220/TO-220FP  
PowerMesh™II MOSFET

TYPE	V <sub>DSS</sub>	R <sub>DS(on)</sub>	I <sub>D</sub>
STP9NC65	650 V	< 0.90 Ω	8 A
STP9NC65FP	650 V	< 0.90 Ω	8 A

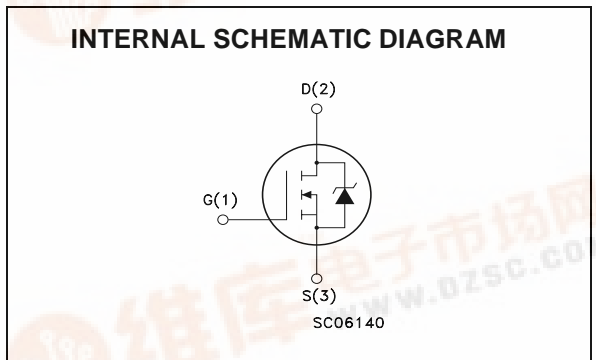
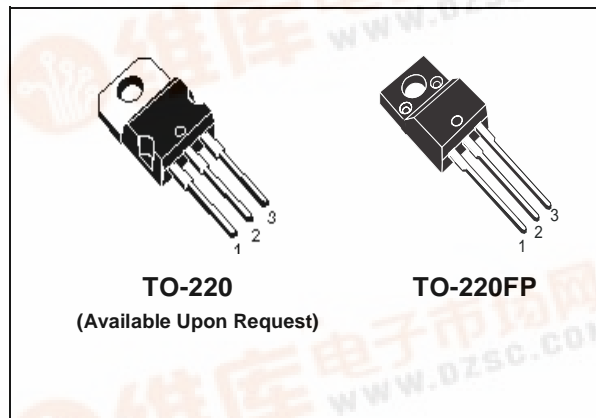
- TYPICAL R<sub>DS(on)</sub> = 0.75 Ω
- EXTREMELY HIGH dv/dt CAPABILITY
- 100% AVALANCHE TESTED
- NEW HIGH VOLTAGE BENCHMARK
- GATE CHARGE MINIMIZED

### DESCRIPTION

The PowerMESH™II is the evolution of the first generation of MESH OVERLAY™. The layout refinements introduced greatly improve the Ron\*area figure of merit while keeping the device at the leading edge for what concerns swithing speed, gate charge and ruggedness.

### APPLICATIONS

- HIGH CURRENT, HIGH SPEED SWITCHING
- SWITCH MODE POWER SUPPLIES (SMPS)
- DC-AC CONVERTERS FOR WELDING EQUIPMENT AND UNINTERRUPTIBLE POWER SUPPLIES AND MOTOR DRIVES



### ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value		Unit
		STP9NC65	STP9NC65FP	
V <sub>DS</sub>	Drain-source Voltage (V <sub>GS</sub> = 0)	650		V
V <sub>DGR</sub>	Drain-gate Voltage (R <sub>GS</sub> = 20 kΩ)	650		V
V <sub>GS</sub>	Gate- source Voltage	±30		V
I <sub>D</sub>	Drain Current (continuous) at T <sub>C</sub> = 25°C	8	8(*)	A
I <sub>D</sub>	Drain Current (continuous) at T <sub>C</sub> = 100°C	5	5(*)	A
I <sub>DM</sub> (●)	Drain Current (pulsed)	32	32(*)	A
P <sub>TOT</sub>	Total Dissipation at T <sub>C</sub> = 25°C	140	40	W
	Derating Factor	1.12	0.32	W/°C
dv/dt (1)	Peak Diode Recovery voltage slope	3.5		V/ns
V <sub>ISO</sub>	Insulation Withstand Voltage (DC)	-	2000	V
T <sub>stg</sub>	Storage Temperature	-65 to 150		°C
T <sub>j</sub>	Max. Operating Junction Temperature	150		°C

(●) Pulse width limited by safe operating area

(\*) Limited only by maximum temperature allowed

(1) I<sub>SD</sub> ≤ 8A, di/dt ≤ 100A/μs, V<sub>DD</sub> ≤ V<sub>(BR)DSS</sub>, T<sub>j</sub> ≤ T<sub>JMAX</sub>.



## STP9NC65/FP

### THERMAL DATA

		TO-220	TO-220FP	
Rthj-case	Thermal Resistance Junction-case Max	0.89	3.12	°C/W
Rthj-amb	Thermal Resistance Junction-ambient Max	62.5		°C/W
Rthc-sink	Thermal Resistance Case-sink Typ	0.5		°C/W
T <sub>I</sub>	Maximum Lead Temperature For Soldering Purpose	300		°C

### AVALANCHE CHARACTERISTICS

Symbol	Parameter	Max Value	Unit
I <sub>AR</sub>	Avalanche Current, Repetitive or Not-Repetitive (pulse width limited by T <sub>j</sub> max)	8	A
E <sub>AS</sub>	Single Pulse Avalanche Energy (starting T <sub>j</sub> = 25 °C, I <sub>D</sub> = I <sub>AR</sub> , V <sub>DD</sub> = 50 V)	850	mJ

### ELECTRICAL CHARACTERISTICS (TCASE = 25 °C UNLESS OTHERWISE SPECIFIED) OFF

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V <sub>(BR)DSS</sub>	Drain-source Breakdown Voltage	I <sub>D</sub> = 250 μA, V <sub>GS</sub> = 0	650			V
I <sub>DSS</sub>	Zero Gate Voltage Drain Current (V <sub>GS</sub> = 0)	V <sub>DS</sub> = Max Rating V <sub>DS</sub> = Max Rating, T <sub>C</sub> = 125 °C			1 50	μA μA
I <sub>GSS</sub>	Gate-body Leakage Current (V <sub>DS</sub> = 0)	V <sub>GS</sub> = ±30V			±100	nA

### ON (1)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250μA	2	3	4	V
R <sub>DS(on)</sub>	Static Drain-source On Resistance	V <sub>GS</sub> = 10V, I <sub>D</sub> = 4.5 A		0.75	0.90	Ω
I <sub>D(on)</sub>	On State Drain Current	V <sub>DS</sub> > I <sub>D(on)</sub> × R <sub>DS(on)</sub> max, V <sub>GS</sub> = 10V	8			A

### DYNAMIC

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
g <sub>fs</sub> (1)	Forward Transconductance	V <sub>DS</sub> > I <sub>D(on)</sub> × R <sub>DS(on)</sub> max, I <sub>D</sub> = 4.5A		10		S
C <sub>iss</sub>	Input Capacitance	V <sub>DS</sub> = 25V, f = 1 MHz, V <sub>GS</sub> = 0		1400		pF
C <sub>OSS</sub>	Output Capacitance			196		pF
C <sub>rSS</sub>	Reverse Transfer Capacitance			31		pF

**ELECTRICAL CHARACTERISTICS (CONTINUED)**

**SWITCHING ON**

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on Delay Time	$V_{DD} = 325\text{ V}$ , $I_D = 4.5\text{ A}$ $R_G = 4.7\Omega$ , $V_{GS} = 10\text{ V}$ (see test circuit, Figure 3)		28		ns
$t_r$	Rise Time			15		ns
$Q_g$	Total Gate Charge	$V_{DD} = 520\text{ V}$ , $I_D = 9\text{ A}$ , $V_{GS} = 10\text{ V}$		44	62	nC
$Q_{gs}$	Gate-Source Charge			10.5		nC
$Q_{gd}$	Gate-Drain Charge			19.5		nC

**SWITCHING OFF**

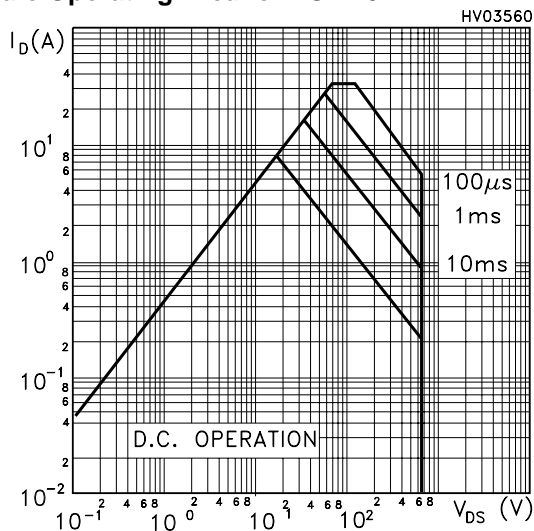
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(off)}$	Turn-Off Delay Time	$V_{DD} = 325\text{ V}$ , $I_D = 4.5\text{ A}$ , $R_G = 4.7\Omega$ , $V_{GS} = 10\text{ V}$ (see test circuit, Figure 3)		53		ns
$t_f$	Fall Time			30		ns
$t_{r(Voff)}$	Off-voltage Rise Time	$V_{DD} = 520\text{ V}$ , $I_D = 9\text{ A}$ , $R_G = 4.7\Omega$ , $V_{GS} = 10\text{ V}$ (see test circuit, Figure 5)		15		ns
$t_f$	Fall Time			12		ns
$t_c$	Cross-over Time			24		ns

**SOURCE DRAIN DIODE**

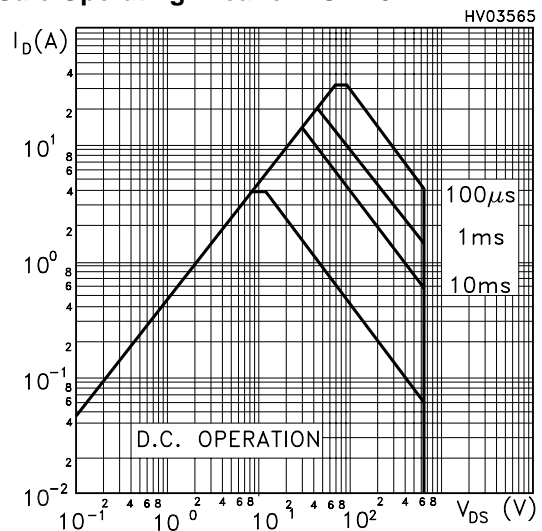
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$I_{SD}$	Source-drain Current				8	A
$I_{SDM(2)}$	Source-drain Current (pulsed)				32	A
$V_{SD(1)}$	Forward On Voltage	$I_{SD} = 8\text{ A}$ , $V_{GS} = 0$			1.6	V
$t_{rr}$	Reverse Recovery Time	$I_{SD} = 9\text{ A}$ , $di/dt = 100\text{ A}/\mu\text{s}$ $V_{DD} = 100\text{ V}$ , $T_j = 150^\circ\text{C}$ (see test circuit, Figure 5)		610		ns
$Q_{rr}$	Reverse Recovery Charge			5.14		$\mu\text{C}$
$I_{RRM}$	Reverse Recovery Current			17		A

Note: 1. Pulsed: Pulse duration = 300  $\mu\text{s}$ , duty cycle 1.5 %.  
2. Pulse width limited by safe operating area.

**Safe Operating Area for TO-220**

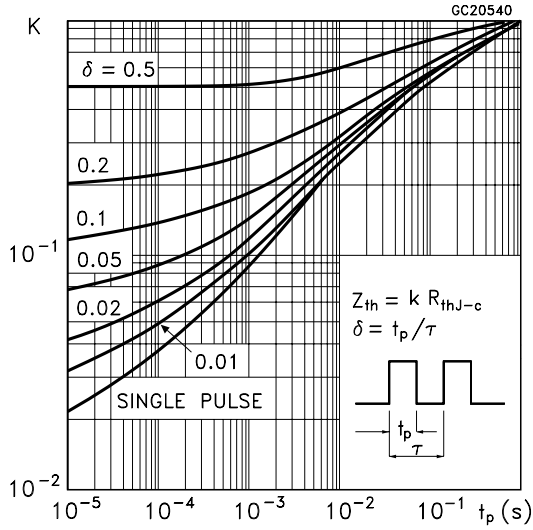


**Safe Operating Area for TO-220FP**

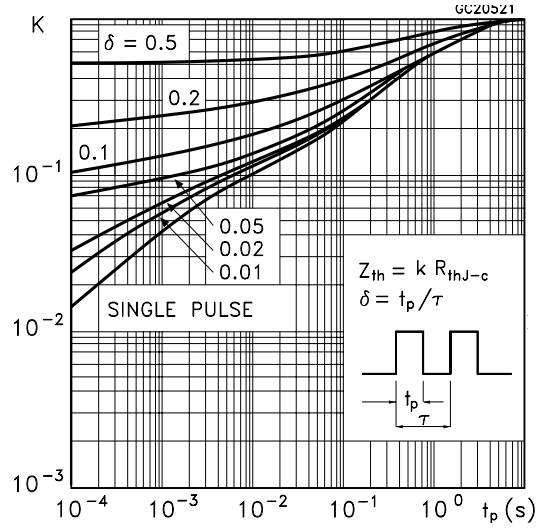


# STP9NC65/FP

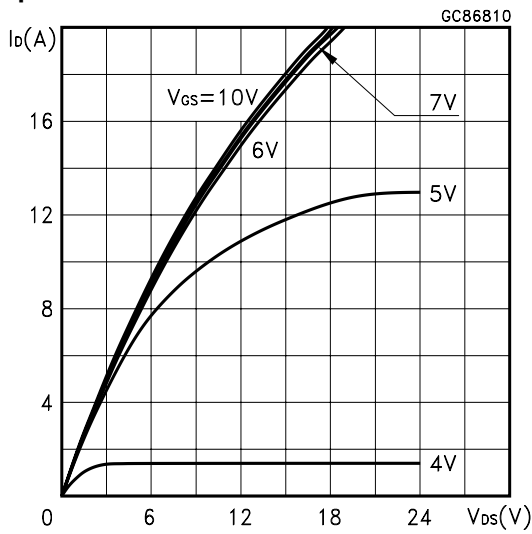
### Thermal Impedance for TO-220



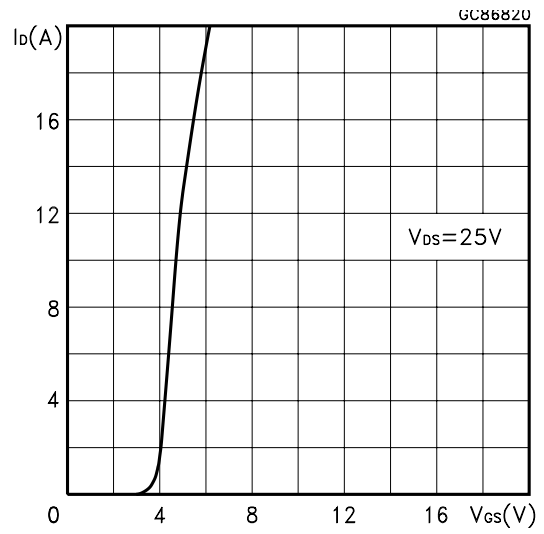
### Thermal Impedance for TO-220FP



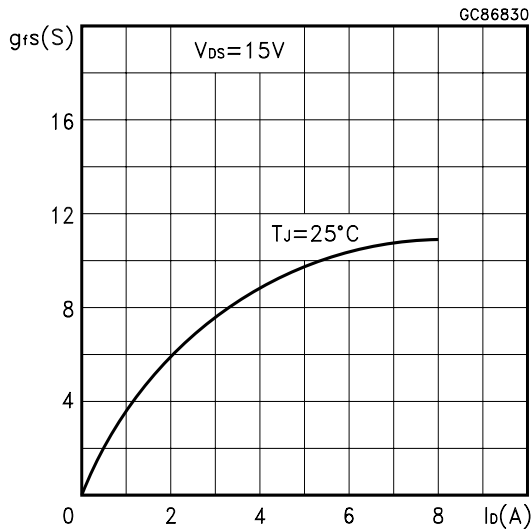
### Output Characteristics



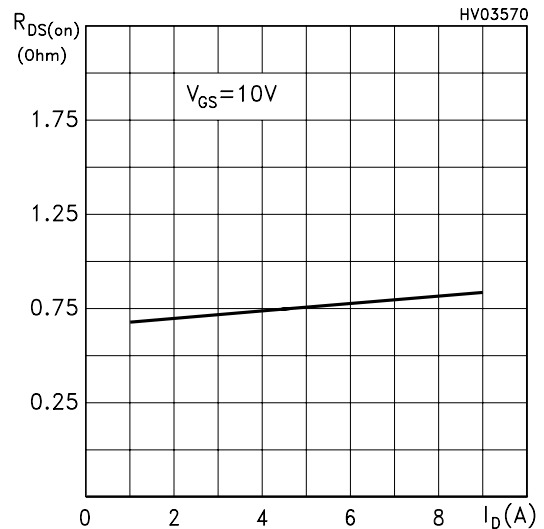
### Transfer Characteristics



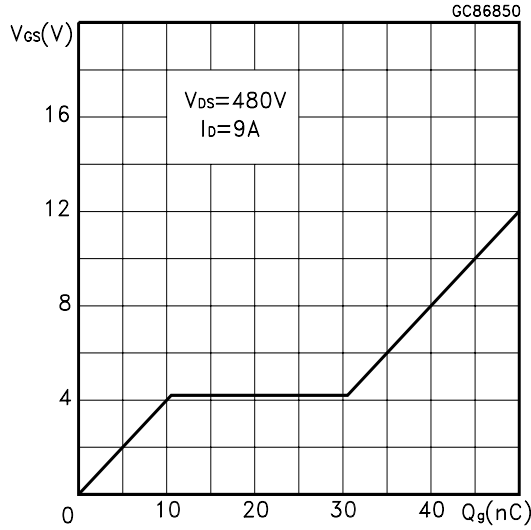
### Transconductance



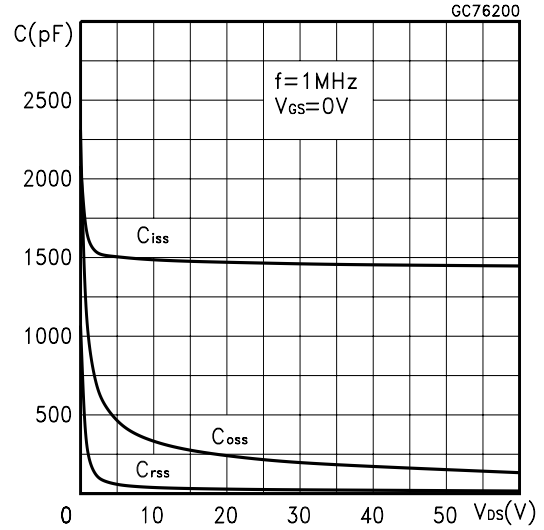
### Static Drain-source On Resistance



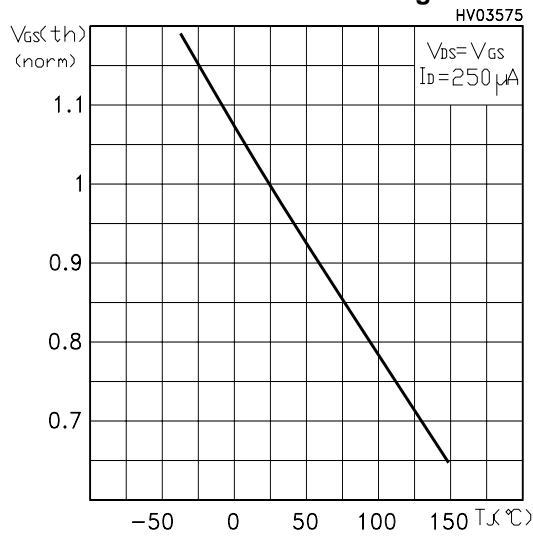
Gate Charge vs Gate-source Voltage



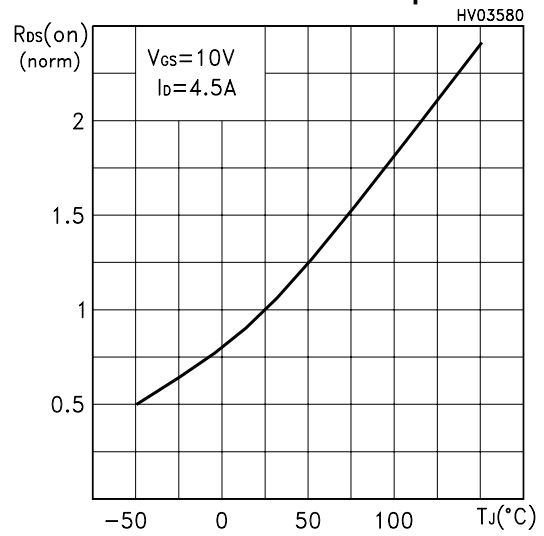
Capacitance Variations



Normalized Gate Threshold Voltage vs Temp.



Normalized On Resistance vs Temperature



Source-drain Diode Forward Characteristics

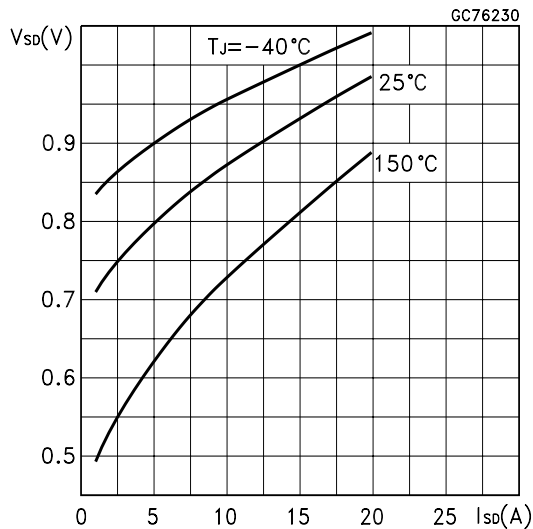


Fig. 1: Unclamped Inductive Load Test Circuit

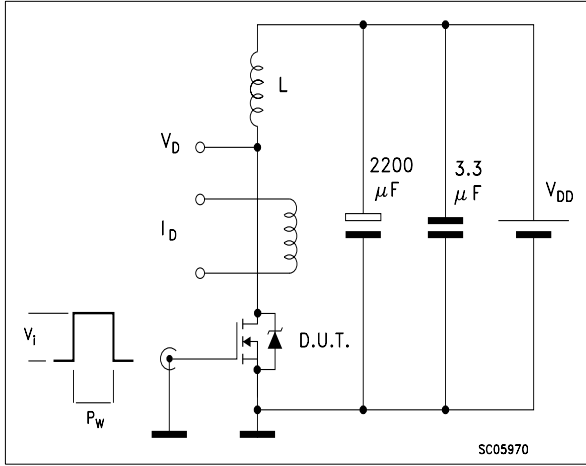


Fig. 2: Unclamped Inductive Waveform

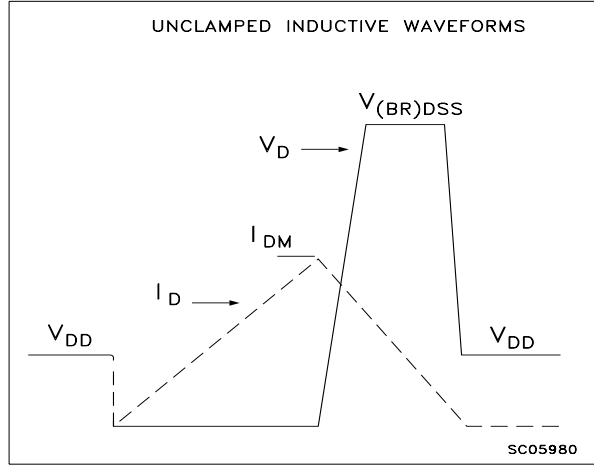


Fig. 3: Switching Times Test Circuit For Resistive Load

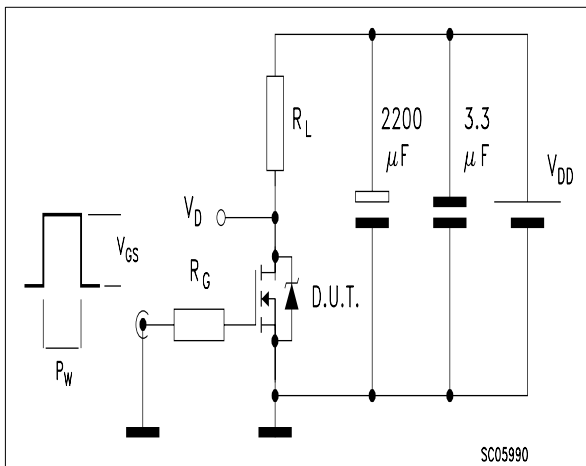


Fig. 4: Gate Charge test Circuit

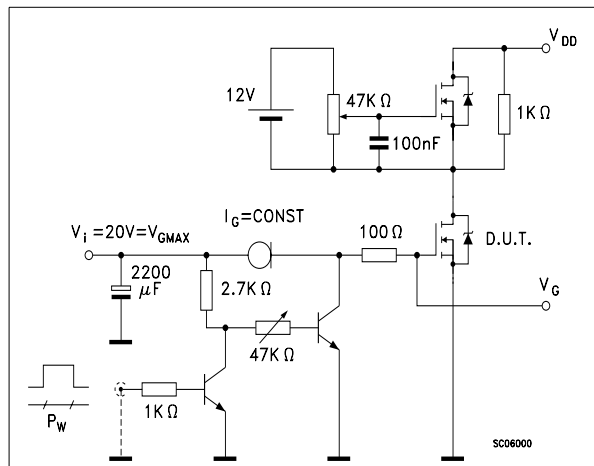
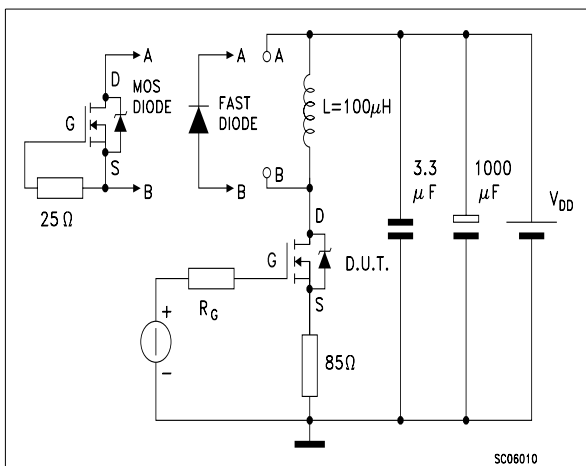
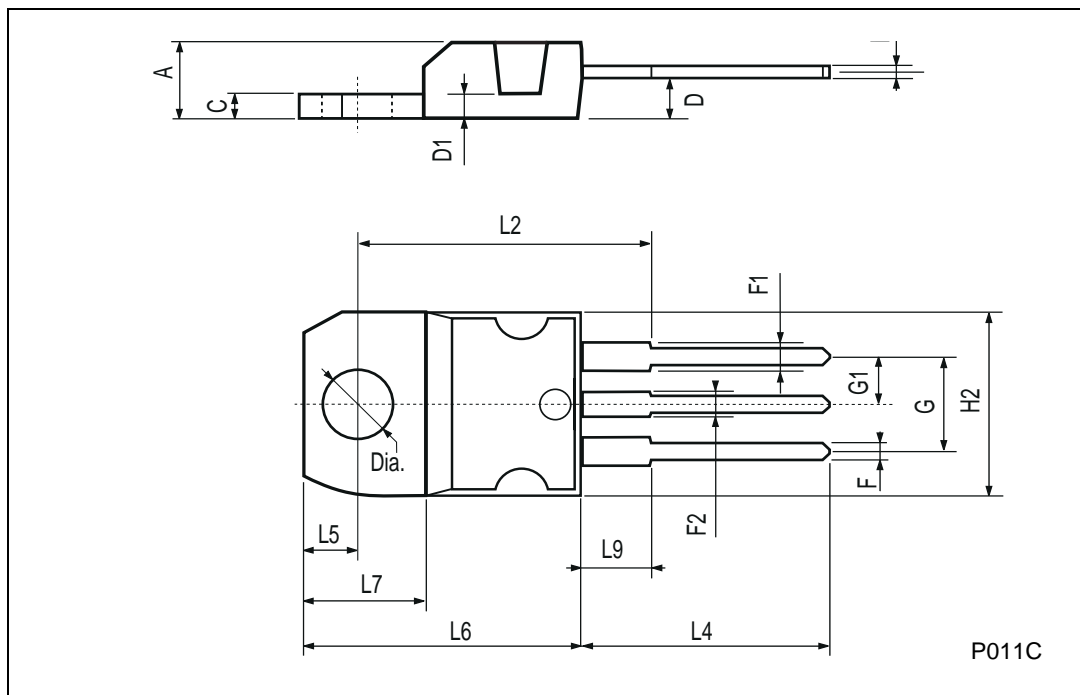


Fig. 5: Test Circuit For Inductive Load Switching And Diode Recovery Times



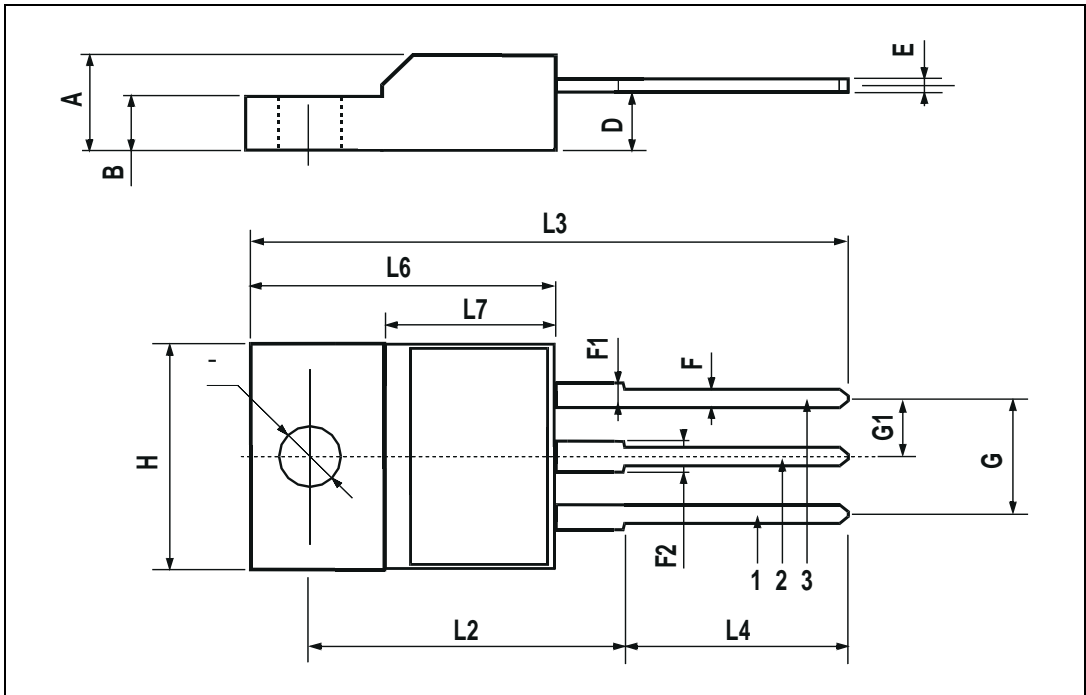
## TO-220 MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	4.40		4.60	0.173		0.181
C	1.23		1.32	0.048		0.051
D	2.40		2.72	0.094		0.107
D1		1.27			0.050	
E	0.49		0.70	0.019		0.027
F	0.61		0.88	0.024		0.034
F1	1.14		1.70	0.044		0.067
F2	1.14		1.70	0.044		0.067
G	4.95		5.15	0.194		0.203
G1	2.4		2.7	0.094		0.106
H2	10.0		10.40	0.393		0.409
L2		16.4			0.645	
L4	13.0		14.0	0.511		0.551
L5	2.65		2.95	0.104		0.116
L6	15.25		15.75	0.600		0.620
L7	6.2		6.6	0.244		0.260
L9	3.5		3.93	0.137		0.154
DIA.	3.75		3.85	0.147		0.151



**TO-220FP MECHANICAL DATA**

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	4.4		4.6	0.173		0.181
B	2.5		2.7	0.098		0.106
D	2.5		2.75	0.098		0.108
E	0.45		0.7	0.017		0.027
F	0.75		1	0.030		0.039
F1	1.15		1.7	0.045		0.067
F2	1.15		1.7	0.045		0.067
G	4.95		5.2	0.195		0.204
G1	2.4		2.7	0.094		0.106
H	10		10.4	0.393		0.409
L2		16			0.630	
L3	28.6		30.6	1.126		1.204
L4	9.8		10.6	0.385		0.417
L6	15.9		16.4	0.626		0.645
L7	9		9.3	0.354		0.366
Ø	3		3.2	0.118		0.126





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